Product data sheet

1. General description

Planar passivated four quadrant triac in a SOT223 surface-mountable plastic package. This very sensitive gate "series D" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

2. Features and benefits

- Direct interfacing to logic level ICs
- · Direct interfacing to low power gate drivers and microcontrollers
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- Triggering in all four quadrants
- Very sensitive gate

3. Applications

- · AC Fan controller
- General purpose low power phase control
- · General purpose low power switching

4. Quick reference data

Table 1. Quick reference data

	t rotorottoo data		 _			_
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{sp} \le 107 ^{\circ}\text{C}$; Fig. 2; Fig. 3	-	-	0.8	А
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5	-	-	9	А
		full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms	-	-	10	Α
Tj	junction temperature		-	-	125	°C
Static charac	teristics					
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 9</u>	-	1	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 9$	-	2	5	mA

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 9}}{}$	-	2	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+;$ $T_j = 25 \text{ °C}; Fig. 9$	-	4	7	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 11</u>	_	1	10	mA
V_{T}	on-state voltage	I _T = 0.85 A; T _j = 25 °C; <u>Fig. 12</u>	-	1.35	1.6	V
Dynamic chara	acteristics					,
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 110 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	30	45	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	V_D = 600 V; T_j = 50 °C; dI_{com}/dt = 0.3 A/ms; I_T = 0.84 A; gate open circuit	-	5	-	V/µs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	4	T2——T1
2	T2	main terminal 2		G sym051
3	G	gate		symosi
4	T2	main terminal 2	⊟1 ⊟2 ⊟3 SC-73 (SOT223)	

6. Ordering information

Table 3. Ordering information

Type number	Package	kage				
	Name	Description	Version			
BT1308W-600D	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223			

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{sp} \le 107 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3	-	0.8	Α
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	9	Α
		full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms	-	10	Α
I ² t	I ² t for fusing	t _p = 10 ms; SIN	-	0.32	A²s
dl _T /dt	rate of rise of on-state	I _G = 20 mA; T2+ G+	-	50	A/µs
	current	I _G = 20 mA; T2+ G-	-	50	A/µs
		I _G = 20 mA; T2- G-	-	50	A/µs
		I _G = 20 mA; T2- G+	-	10	A/µs
I _{GM}	peak gate current		-	1	Α
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.1	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

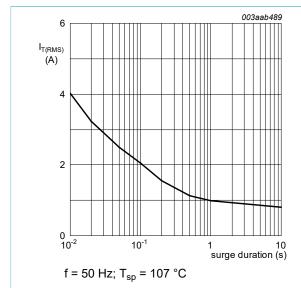


Fig. 1. RMS on-state current as a function of surge duration; maximum values

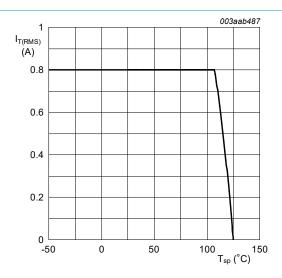


Fig. 2. RMS on-state current as a function of solder point temperature; maximum values

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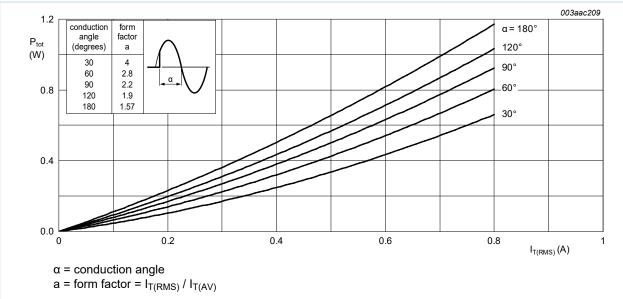


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

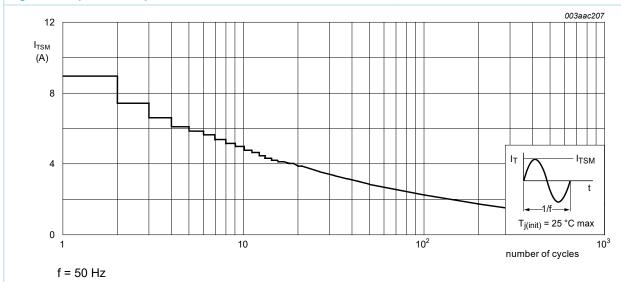
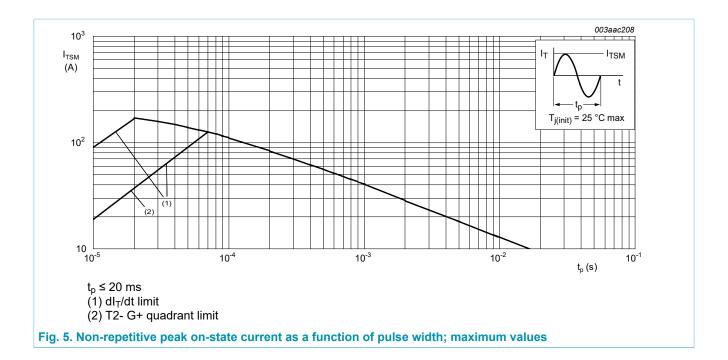


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	full cycle; Fig. 6	-	-	15	K/W
R _{th(j-a)}	thermal resistance	full cycle; for minimum footprint; Fig. 7	-	156	-	K/W
	from junction to ambient free air	full cycle; for pad area; Fig. 8	-	70	-	K/W

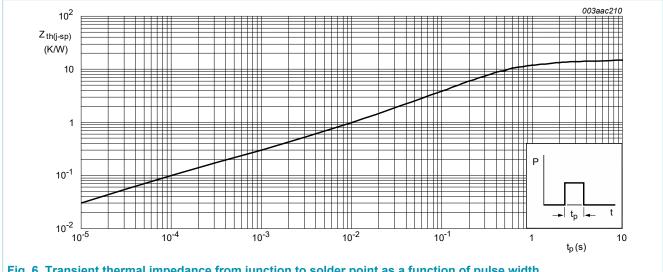
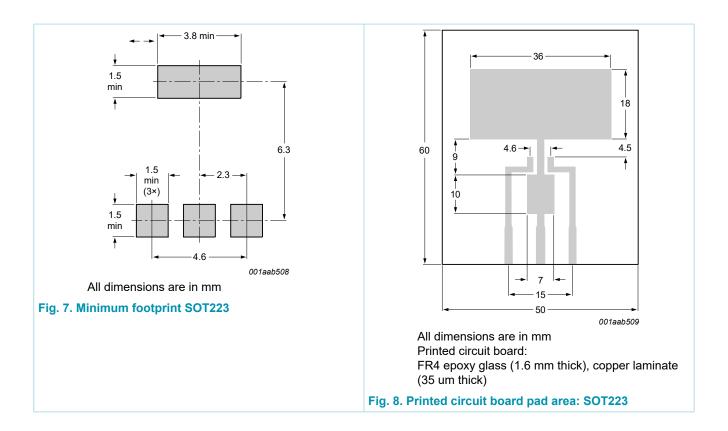


Fig. 6. Transient thermal impedance from junction to solder point as a function of pulse width

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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics				,	,
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 9$	-	1	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 9$	-	2	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 9}}{}$	-	2	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 9}}{}$	-	4	7	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 10$	-	1	10	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 10$	-	5	10	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. } 10}{\text{ C}}$	-	1	10	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. } 10}{\text{ C}}$	-	2	10	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 11</u>	-	1	10	mA
V_{T}	on-state voltage	I _T = 0.85 A; T _j = 25 °C; <u>Fig. 12</u>	-	1.35	1.6	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 13	-	0.9	1.5	V
		$V_D = 600 \text{ V}; I_T = 0.1 \text{ A}; T_j = 110 \text{ °C};$ Fig. 13	0.1	0.7	-	V
I _D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic ch	naracteristics		•		,	
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 110 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	30	45	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	V_D = 600 V; T_j = 50 °C; dI_{com}/dt = 0.3 A/ms; I_T = 0.84 A; gate open circuit	-	5	-	V/µs
t _{gt}	gate-controlled turn-on time	I_{TM} = 1 A; V_D = 600 V; I_G = 25 mA; $dI_G/$ dt = 5 A/µs	-	2	-	μs

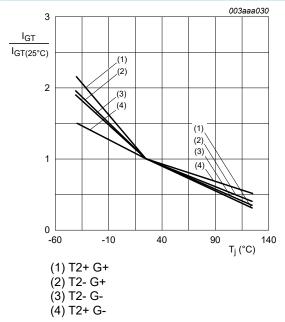


Fig. 9. Normalized gate trigger current as a function of junction temperature

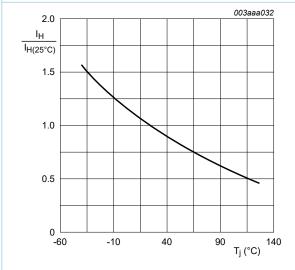


Fig. 11. Normalized holding current as a function of junction temperature

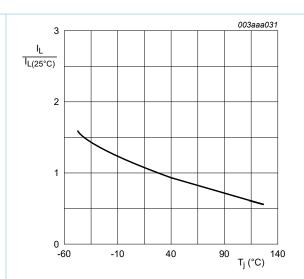
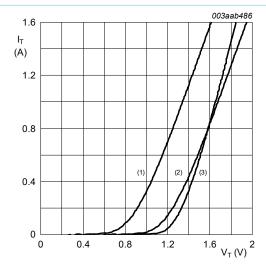


Fig. 10. Normalized latching current as a function of junction temperature



 V_o = 1.171 V; R_s = 0.5125 Ω (1) T_j = 125 °C; typical values (2) T_j = 125 °C; maximum values (3) T_j = 25 °C; maximum values

Fig. 12. On-state current as a function of on-state voltage

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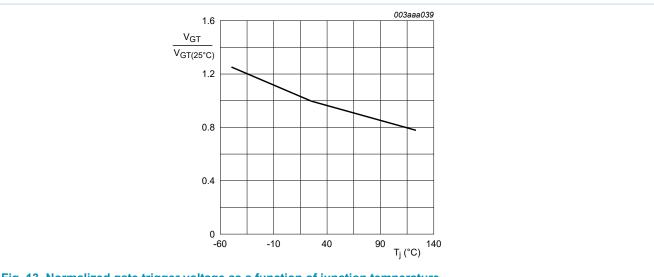


Fig. 13. Normalized gate trigger voltage as a function of junction temperature

10. Package outline

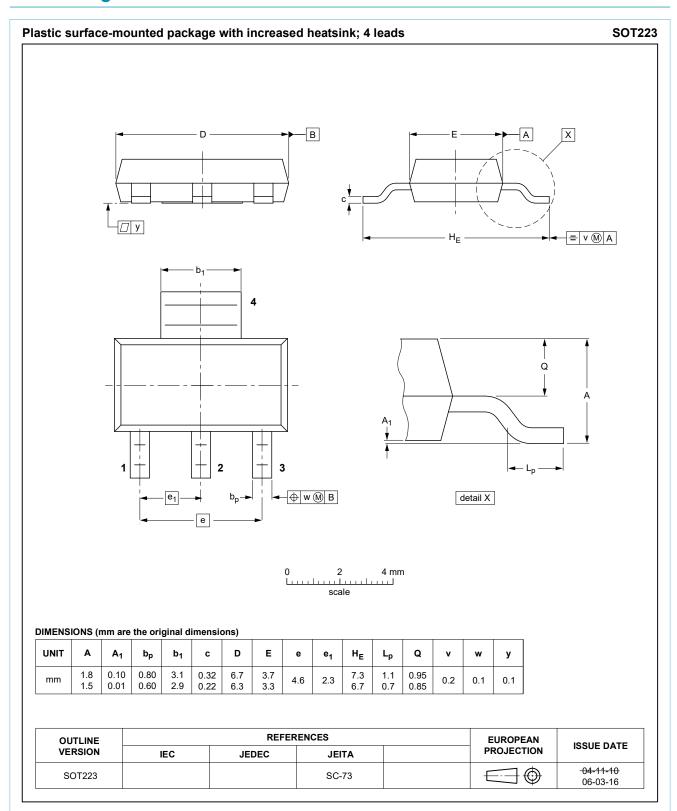


Fig. 14. Package outline SC-73 (SOT223)

11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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